

Dear Editor,

We are pleased to submit our manuscript "Theoretical approach towards rational design and characterization of benzo[1,2-b:5-B']dithiophene (BDT)-based (A-D-A) small molecules of relevance for high performance solar cells " for publication in the Journal of Material Sciences & Engineering.

Recently, organic materials, including conjugated polymers, organic small molecules and self-assembling organic semiconductors, have intrigued an increasing attention because of their potential to enable the fabrication of flexible, light weight, semi transparency and large-area devices. Among several designed SMs for solution processed solar cells, those including benzo[1,2-b:5-B']dithiophene (BDT) have been emerging as an attractive building block for donor molecules in OPVs. In this context, a PCE of 9.2% was recently achieved in an OPV device based on BDTT-S-TR/PC₇₀BM. In this paper, a series of BDT-based small molecules with acceptor-donor-acceptor (A-D-A) structure were designed based on the experimental system BDTT-S-TR (**1**) for use as potential donor materials for organic photovoltaic (OPV) devices. Their geometry structures, electronic, optical and photovoltaic properties have been investigated by means of density functional theory (DFT) and time dependent density functional theory (TDDFT) methods. The purpose was double; to optimize the energy levels with those of PC₇₀BM and to increase the performance in OPV devices. From this regard, we have predicted the PCEs of the OPVs based on **1-4/PC₇₀BM** using Marks model and the results show significant improvement in PCEs compared to the reported system **1/PC₇₀BM**. The charge transfer dynamics, including intermolecular charge transfer (inter-CT) and recombination (inter-CR) rates, in **1-4/PC₇₀BM** heterojunctions have been examined. The calculations show that the ratio $k_{inter-CT} / k_{inter-CR}$ for the **3/PC₇₀BM** and **4/PC₇₀BM** heterojunction is $\sim 10^4$ times higher than that of the **1/PC₇₀BM**.

Consequently, we have identified two new promising photovoltaic donor material (**3** and **4**) for high-efficiency SMs OPVs materials and we hope that this computational study may stimulate experimentalists to synthesize and study these new small molecules; structural parameters, optical and photovoltaic properties were computed, which will facilitate future experimental work.

The manuscript is original and no part of it has been published before, nor is any part of under consideration for publication at another journal.

Yours sincerely,

The authors

Electronic Supplementary Information (ESI)

Theoretical approach towards rational design and characterization of benzo[1,2-b:5-B']dithiophene (BDT)-based (A-D-A) small molecules of relevance for high performance solar cells

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	B3LYP	PBE0	B3PW91	Exp in ref [14]
HOMO (eV)	-5.03	-5.20	-5.16	-5.18

Table S1. The HOMO energy (eV) of **1** calculated by different functionals B3LYP, B3PW91 and PBE0 with 6-31G(d) basis set compared with the experimental data.

	B3PW91	M06	M062X	CAM-B3LYP	WB97X(D)	BHandHLYP	Exp in ref [14]
$\lambda_{S_0-S_1}$ (nm)	687	639	523	522	504	538	506
$E_{S_0-S_1}$ (eV)	1.80	1.94	2.37	2.37	2.46	2.30	2.45

Table S2. The first singlet excitation energies ($E_{S_0-S_1}$ (eV)) and the corresponding absorption wavelength ($\lambda_{S_0-S_1}$ (nm)) calculated by different functionals with the 6-31G(d) basis set based on the optimized geometry in vacuum at B3PW91/6-31G(d). The calculated values are compared with the experimental data taken from ref 14.

	PBE0	M06	M062X	CAM-B3LYP	WB97X(D)	BHandHLYP	Exp in ref [14]
$\lambda_{S_0-S_1}$ (nm)	638	632	517	516	498	531	506
$E_{S_0-S_1}$ (eV)	1.94	1.96	2.40	2.40	2.49	2.33	2.45

Table S3. The first singlet excitation energies ($E_{S_0-S_1}$ (eV)) and the corresponding absorption wavelength ($\lambda_{S_0-S_1}$ (nm)) calculated by different functionals with the 6-31G(d) basis set based on the optimized geometry in vacuum at PBE0/6-31G(d). The calculated values are compared with the experimental data taken from ref 14.

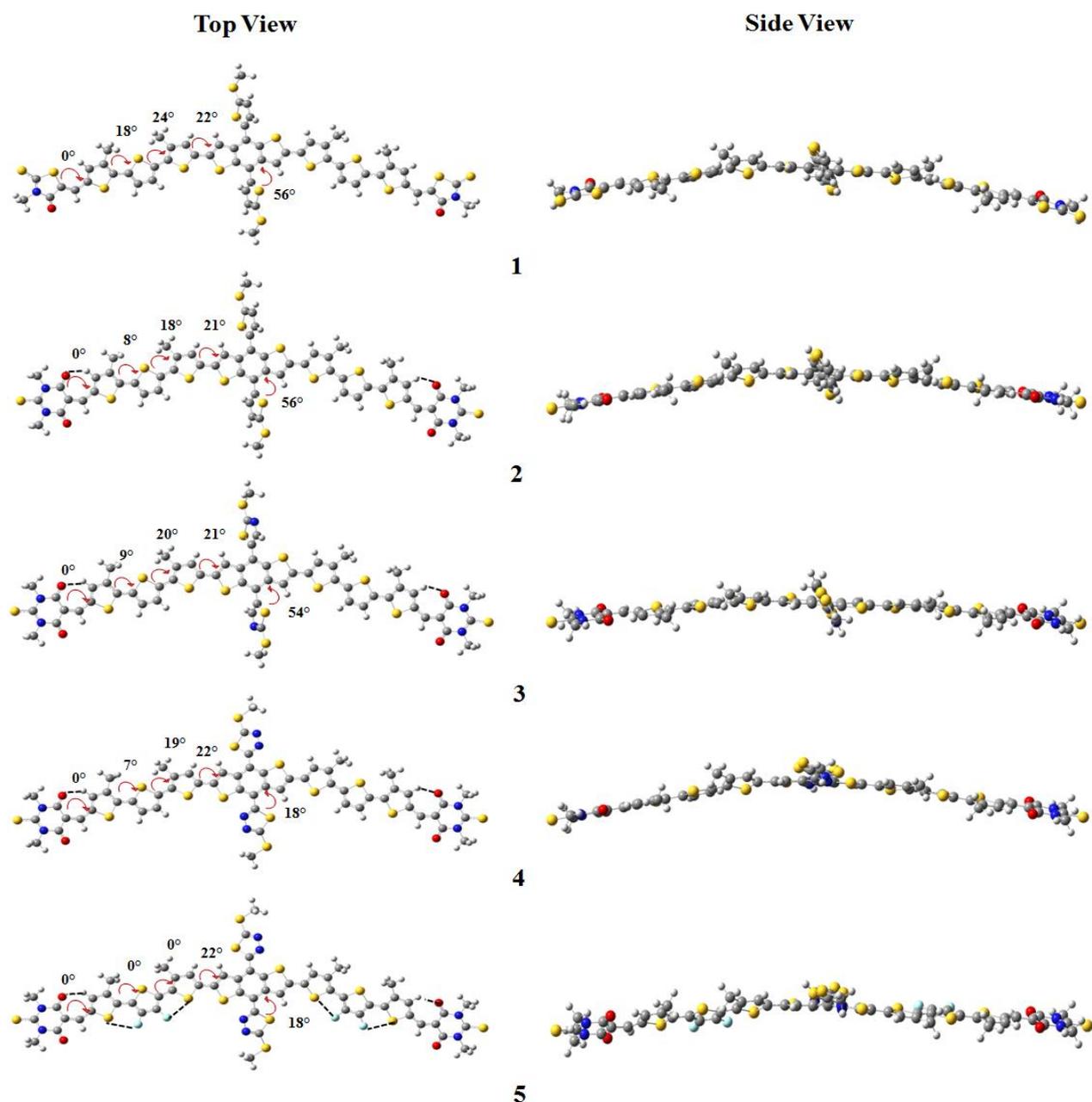


Figure S1. Optimized geometries of SMs 1-5 at the B3PW91/6-31G(d) level of theory with the dihedral angles between donor and acceptor units.

	1/PC₇₀BM		
	E/eV (λ/nm)	f	Excited-state property
S₁	2.33 (532)	0.0023	Local excited (LE) transition on PC ₇₀ BM
S₂	2.48 (499)	0.0138	Local excited (LE) transition on PC ₇₀ BM
S₃	2.49 (497)	4.6336	Local excited (LE) transition on 1
S₄	2.60 (477)	0.0355	Local excited (LE) transition on PC ₇₀ BM
S₅	2.65 (468)	0.0160	Local excited (LE) transition on PC ₇₀ BM
S₆	2.70 (458)	0.2175	Local excited (LE) transition on 1
S₇	2.77 (446)	0.0305	Local excited (LE) transition on PC ₇₀ BM
S₈	2.83 (437)	0.0030	Local excited (LE) transition on PC ₇₀ BM
S₉	2.85 (433)	0.0051	Local excited (LE) transition on PC ₇₀ BM
S₁₀	2.86 (433)	0.0086	Local excited (LE) transition on PC ₇₀ BM
S₁₁	2.88 (429)	0.0049	Local excited (LE) transition on PC ₇₀ BM
S₁₂	2.91 (425)	0.0073	Local excited (LE) transition on PC ₇₀ BM
S₁₃	2.96 (419)	0.0005	Local excited (LE) transition on PC ₇₀ BM
S₁₄	3.00 (413)	0.0024	Local excited (LE) transition on PC ₇₀ BM
S₁₅	3.02 (410)	0.0003	Local excited (LE) transition on PC ₇₀ BM
S₁₆	3.04 (407)	0.0000	Intermolecular charge transfer (inter-CT)
S₁₇	3.05 (406)	0.0002	Local excited (LE) transition on PC ₇₀ BM
S₁₈	3.09 (400)	0.0014	Local excited (LE) transition on PC ₇₀ BM
S₁₉	3.10 (400)	0.0015	Local excited (LE) transition on PC ₇₀ BM
S₂₀	3.12 (398)	0.0163	Local excited (LE) transition on PC ₇₀ BM

Table S4. Calculated electronic transition energies (eV) and corresponding excitation oscillator strengths (f) for **1/PC₇₀BM** heterojunction at TDDFT/CAM-B3LYP/6-31G(d).

	2/PC₇₀BM		
	E/eV (λ/nm)	f	Excited-state property
S₁	2.32 (533)	0.0031	Local excited (LE) transition on PC ₇₀ BM
S₂	2.42 (512)	4.3257	Local excited (LE) transition on 2
S₃	2.48 (500)	0.0614	Local excited (LE) transition on PC ₇₀ BM
S₄	2.59 (478)	0.1014	Local excited (LE) transition on PC ₇₀ BM
S₅	2.63 (470)	0.5767	Local excited (LE) transition on 2
S₆	2.65 (468)	0.0049	Local excited (LE) transition on PC ₇₀ BM
S₇	2.77 (448)	0.0295	Local excited (LE) transition on PC ₇₀ BM
S₈	2.83 (438)	0.0024	Local excited (LE) transition on PC ₇₀ BM
S₉	2.85 (434)	0.0046	Local excited (LE) transition on PC ₇₀ BM
S₁₀	2.86 (433)	0.0099	Local excited (LE) transition on PC ₇₀ BM
S₁₁	2.87 (432)	0.0013	Pure Intermolecular charge transfer
S₁₂	2.88 (431)	0.0024	Local excited (LE) transition on PC ₇₀ BM
S₁₃	2.91 (426)	0.0086	Local excited (LE) transition on PC ₇₀ BM
S₁₄	2.96 (419)	0.0006	Local excited (LE) transition on PC ₇₀ BM
S₁₅	3.00 (413)	0.0017	Local excited (LE) transition on PC ₇₀ BM
S₁₆	3.02 (410)	0.0003	Pure Intermolecular charge transfer
S₁₇	3.05 (405)	0.0001	Local excited (LE) transition on PC ₇₀ BM
S₁₈	3.08 (401)	0.0002	Local excited (LE) transition on PC ₇₀ BM
S₁₉	3.09 (401)	0.0017	Local excited (LE) transition on PC ₇₀ BM
S₂₀	3.10 (400)	0.0011	Local excited (LE) transition on PC ₇₀ BM

Table S5. Calculated electronic transition energies (eV) and corresponding excitation oscillator strengths (f) for **2/PC₇₀BM** heterojunction at TDDFT/CAM-B3LYP/6-31G(d).

3/PC₇₀BM			
	E/eV (λ/nm)	f	Excited-state property
S₁	2.33 (532)	0.0020	Local excited (LE) transition on PC ₇₀ BM
S₂	2.44 (508)	4.5200	Local excited (LE) transition on 3
S₃	2.47 (502)	0.0759	Local excited (LE) transition on PC ₇₀ BM
S₄	2.60 (477)	0.0842	Local excited (LE) transition on PC ₇₀ BM
S₅	2.64 (470)	0.3286	Local excited (LE) transition on 3
S₆	2.65 (467)	0.0187	Local excited (LE) transition on PC ₇₀ BM
S₇	2.77 (448)	0.0285	Local excited (LE) transition on PC ₇₀ BM
S₈	2.83 (438)	0.0019	Local excited (LE) transition on PC ₇₀ BM
S₉	2.85 (435)	0.0069	Local excited (LE) transition on PC ₇₀ BM
S₁₀	2.86 (433)	0.0023	Intermolecular charge transfer (inter-CT)
S₁₁	2.87 (433)	0.0096	Local excited (LE) transition on PC ₇₀ BM
S₁₂	2.88 (430)	0.0053	Local excited (LE) transition on PC ₇₀ BM
S₁₃	2.91 (425)	0.0054	Local excited (LE) transition on PC ₇₀ BM
S₁₄	2.96 (418)	0.0005	Local excited (LE) transition on PC ₇₀ BM
S₁₅	3.00 (413)	0.0022	Local excited (LE) transition on PC ₇₀ BM
S₁₆	3.01 (411)	0.0003	Local excited (LE) transition on PC ₇₀ BM
S₁₇	3.06 (404)	0.0003	Intermolecular charge transfer (inter-CT)
S₁₈	3.07 (403)	0.0002	Intermolecular charge transfer (inter-CT)
S₁₉	3.10 (400)	0.0007	Local excited (LE) transition on PC ₇₀ BM
S₂₀	3.10 (400)	0.0034	Local excited (LE) transition on PC ₇₀ BM

Table S6. Calculated electronic transition energies (eV) and corresponding excitation oscillator strengths (f) for **3/PC₇₀BM** heterojunction at TDDFT/CAM-B3LYP/6-31G(d).

	4/PC₇₀BM		
	E/eV (λ/nm)	f	Excited-state property
S₁	2.33 (532)	0.0015	Local excited (LE) transition on PC ₇₀ BM
S₂	2.39 (518)	4.3839	Local excited (LE) transition on 4
S₃	2.47 (502)	0.0507	Local excited (LE) transition on PC ₇₀ BM
S₄	2.56 (477)	0.1359	Local excited (LE) transition on PC ₇₀ BM
S₅	2.62 (473)	0.2554	Local excited (LE) transition on 4
S₆	2.65 (467)	0.0191	Local excited (LE) transition on PC ₇₀ BM
S₇	2.77 (448)	0.0331	Local excited (LE) transition on PC ₇₀ BM
S₈	2.83 (438)	0.0025	Local excited (LE) transition on PC ₇₀ BM
S₉	2.85 (435)	0.0058	Local excited (LE) transition on PC ₇₀ BM
S₁₀	2.86 (432)	0.0130	Local excited (LE) transition on PC ₇₀ BM
S₁₁	2.87 (431)	0.0003	Local excited (LE) transition on PC ₇₀ BM
S₁₂	2.90 (427)	0.0102	Intermolecular charge transfer (inter-CT)
S₁₃	2.94 (421)	0.0008	Intermolecular charge transfer (inter-CT)
S₁₄	2.96 (419)	0.0032	Local excited (LE) transition on PC ₇₀ BM
S₁₅	2.98 (415)	0.3687	Local excited (LE) transition on 4
S₁₆	3.00 (413)	0.0027	Local excited (LE) transition on PC ₇₀ BM
S₁₇	3.01 (411)	0.0016	Intermolecular charge transfer (inter-CT)
S₁₈	3.06 (404)	0.0001	Intermolecular charge transfer (inter-CT)
S₁₉	3.09 (400)	0.0010	Local excited (LE) transition on PC ₇₀ BM
S₂₀	3.10 (400)	0.0045	Local excited (LE) transition on PC ₇₀ BM

Table S7. Calculated electronic transition energies (eV) and corresponding excitation oscillator strengths (f) for **4/PC₇₀BM** heterojunction at TDDFT/CAM-B3LYP/6-31G(d).